2SC2995

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

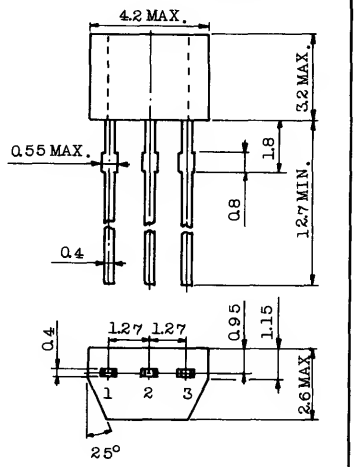
FM/AM RF, MIX, OSC, IF
HIGH FREQUENCY AMPLIFIER APPLICATIONS.

FEATURES:

. High Stability Oscillation Voltage On FM Local Oscillator.

. Recommend FM/AM RF, MIX, OSC and IF.

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	—
EIAJ	—
TOSHIBA	2-4E1A

Weight : 0.13g

MAXIMUM RATINGS (Ta=25 °C)

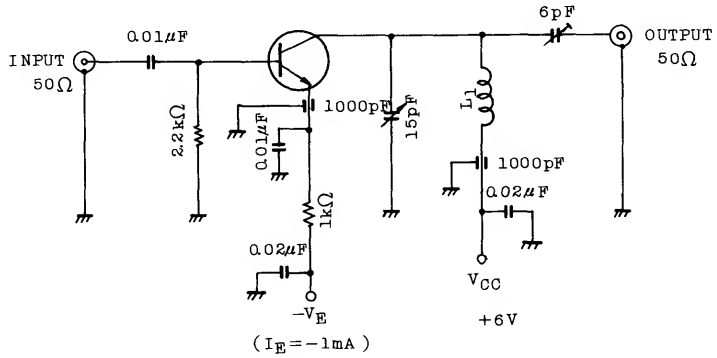
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	50	mA
Emitter Current	I_E	-50	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55 ~ 125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=40V, I_E=0	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=4V, I_C=0	-	-	0.5	μA
DC Current Gain	h_{FE} (Note)	V_{CE}=6V, I_C=1mA	40	-	240	
Reverse Transfer Capacitance	C_{re}	V_{CE}=6V, f=1MHz	-	0.9	1.3	pF
Transition Frequency	f_T	V_{CE}=6V, I_E=-1mA	150	350	-	MHz
Collector-Base Time Constant	$C_{c.rbb'}$	V_{CE}=6V, I_E=-1mA, f=30MHz	-	15	30	ps
Noise Figure	NF	V_{CC}=6V, I_E=-1mA f=100MHz (Fig.1)	-	4.0	-	dB
Power Gain	G_{pe}		-	15	-	
Oscillation Output Voltage	V_{OSC}	V_{CC}=6V, f=100MHz (Fig.2)	-	150	-	mV

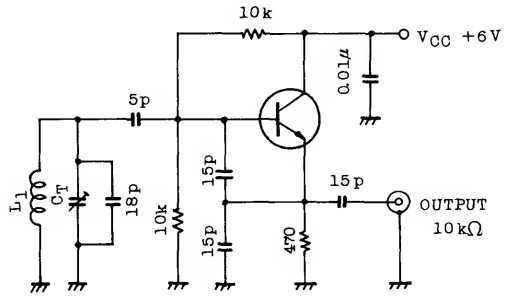
Note : h_{FE} Classification R:40~80 O:70~140 Y:120~240

Fig. 1 NF, G_{pe} TEST CIRCUIT



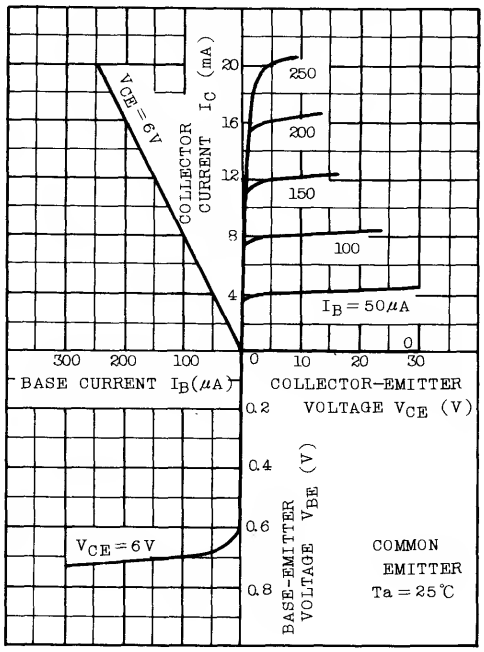
L_1 : 0.8mmφ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

Fig. 2 V_{OSC} TEST CIRCUIT

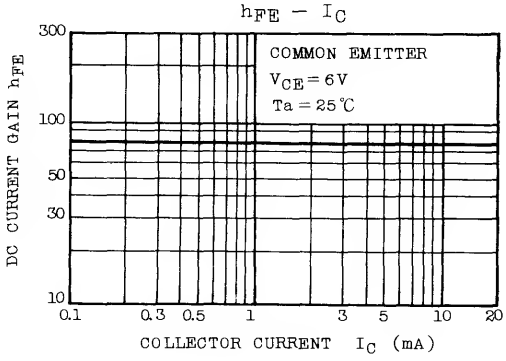


L_1 : 0.8mmφ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

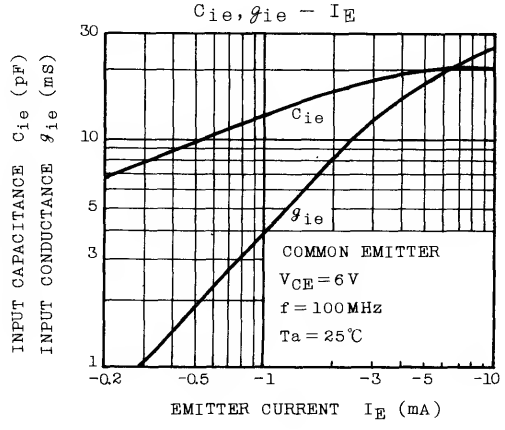
STATIC CHARACTERISTICS



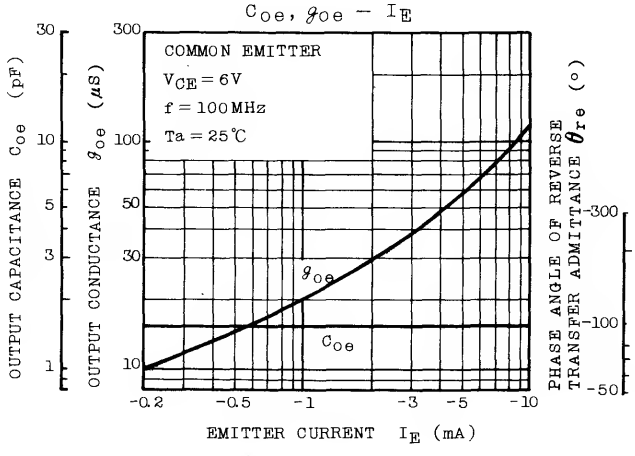
$h_{FE} - I_C$



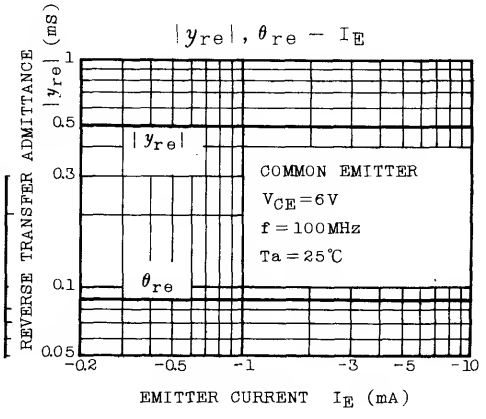
$C_{ie}, g_{ie} - I_E$

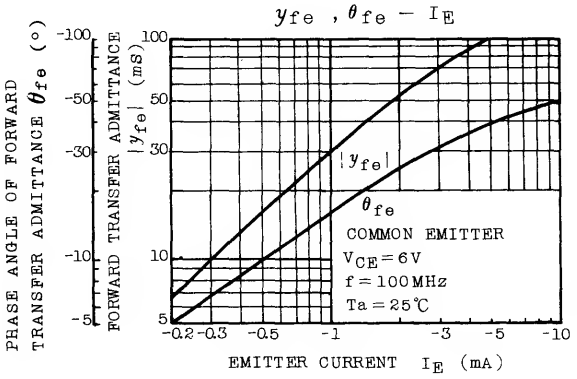


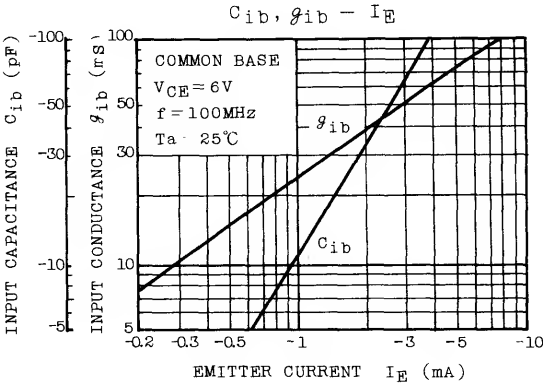
$C_{oe}, g_{oe} - I_E$

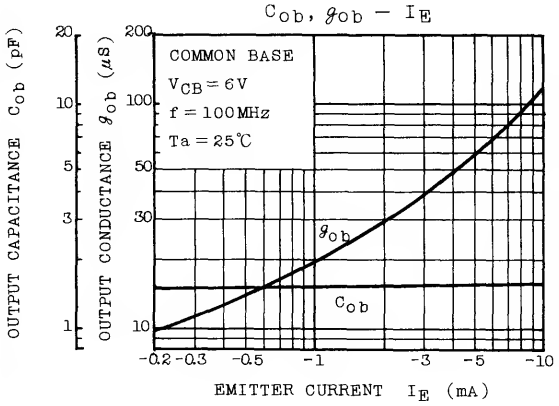


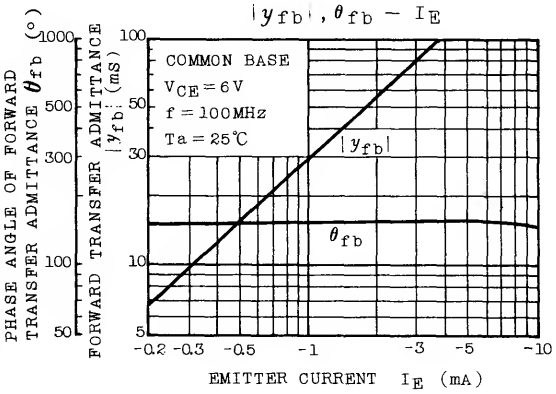
$|y_{re}|, \theta_{re} - I_E$

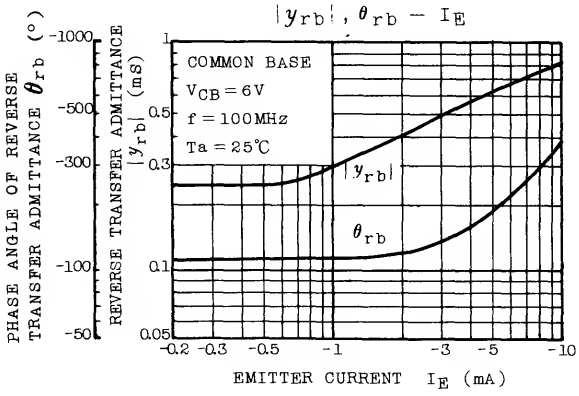


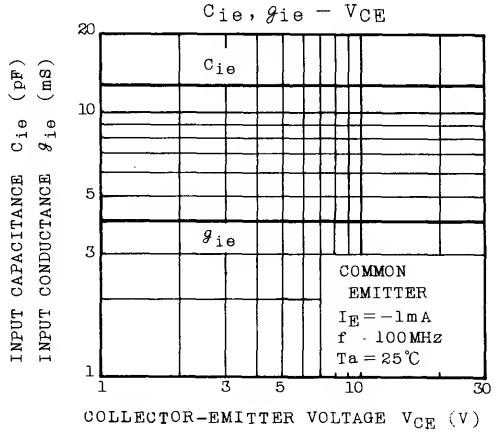

y_{fe} , θ_{fe} – I_E
PHASE ANGLE OF FORWARD TRANSFER ADMITTANCE θ_{fe} (°)
FORWARD TRANSFER ADMITTANCE $|y_{fe}|$ (mS)
$|y_{fe}|$
θ_{fe}
COMMON EMITTER
V_{CE} = 6V
f = 100MHz
Ta = 25℃
EMITTER CURRENT I_E (mA)


C_{ib}, g_{ib} – I_E
INPUT CAPACITANCE C_{ib} (pF)
INPUT CONDUCTANCE g_{ib} (mS)
COMMON BASE
V_{CE} = 6V
f = 100MHz
Ta = 25℃
g_{ib}
C_{ib}
EMITTER CURRENT I_E (mA)

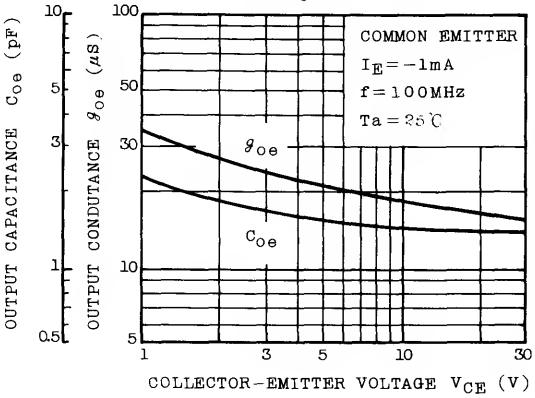

C_{ob}, g_{ob} – I_E
OUTPUT CAPACITANCE C_{ob} (pF)
OUTPUT CONDUCTANCE g_{ob} (μS)
COMMON BASE
V_{CB} = 6V
f = 100MHz
Ta = 25℃
g_{ob}
C_{ob}
EMITTER CURRENT I_E (mA)


$|y_{fb}|$, θ_{fb} – I_E
PHASE ANGLE OF FORWARD TRANSFER ADMITTANCE θ_{fb} (°)
FORWARD TRANSFER ADMITTANCE $|y_{fb}|$ (mS)
COMMON BASE
V_{CE} = 6V
f = 100MHz
Ta = 25℃
$|y_{fb}|$
θ_{fb}
EMITTER CURRENT I_E (mA)

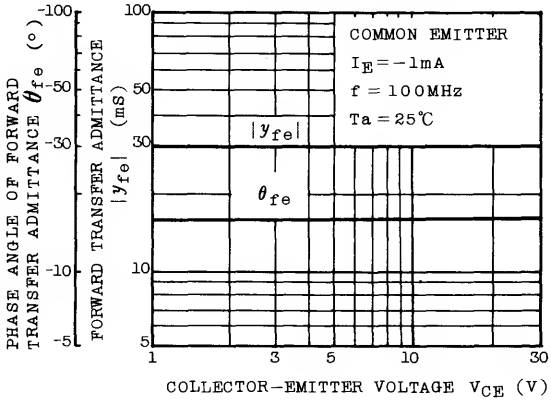

$|y_{rb}|$, θ_{rb} – I_E
PHASE ANGLE OF REVERSE TRANSFER ADMITTANCE θ_{rb} (°)
REVERSE TRANSFER ADMITTANCE $|y_{rb}|$ (mS)
COMMON BASE
V_{CB} = 6V
f = 100MHz
Ta = 25℃
$|y_{rb}|$
θ_{rb}
EMITTER CURRENT I_E (mA)


C_{ie}, g_{ie} – V_{CE}
INPUT CAPACITANCE C_{ie} (pF)
INPUT CONDUCTANCE g_{ie} (mS)
C_{ie}
g_{ie}
COMMON EMITTER
I_E = –1mA
f = 100MHz
Ta = 25℃
COLLECTOR–EMITTER VOLTAGE V_{CE} (V)

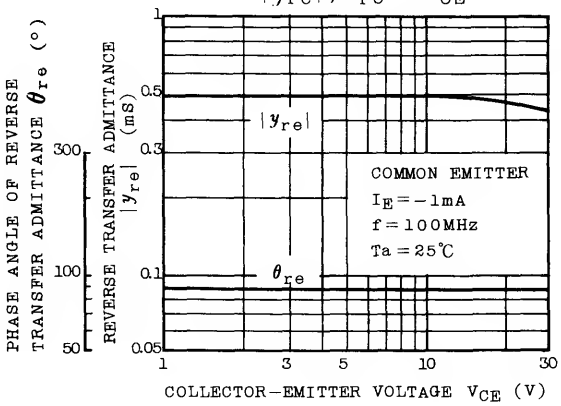
C_{oe}, g_{oe} – V_{CE}



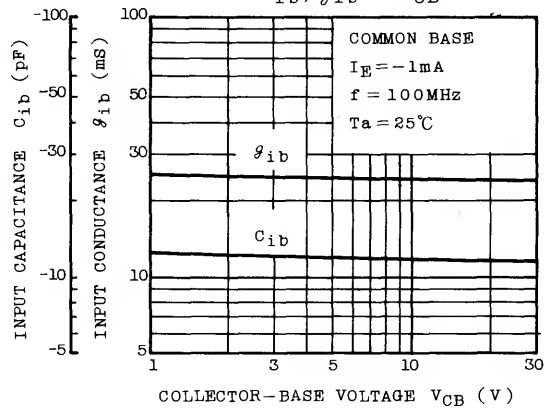
$|y_{fe}|$, θ_{fe} – V_{CE}



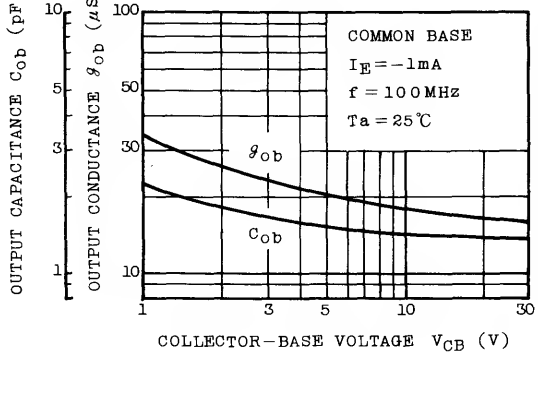
$|y_{re}|$, θ_{re} – V_{CE}



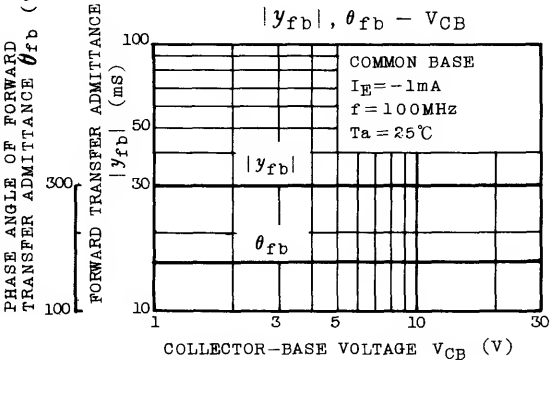
C_{ib}, g_{ib} – V_{CB}

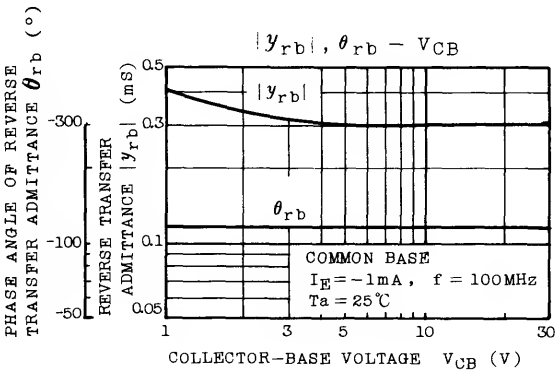


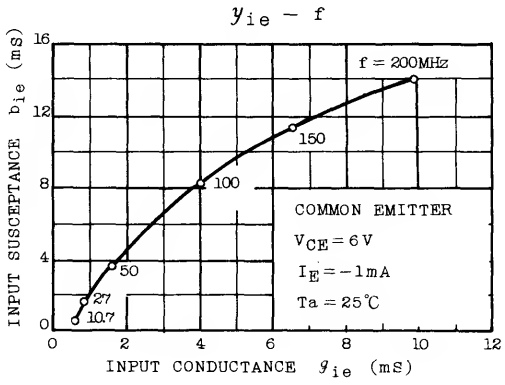
C_{ob}, g_{ob} – V_{CB}

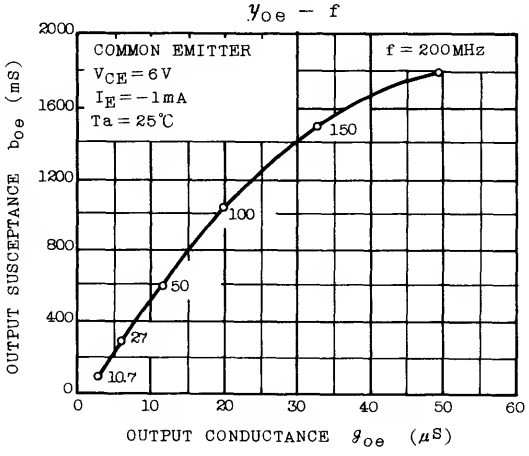


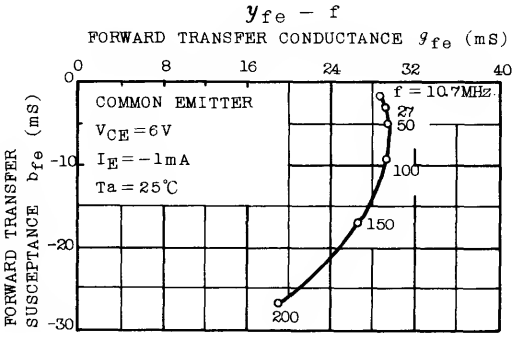
$|y_{fb}|$, θ_{fb} – V_{CB}

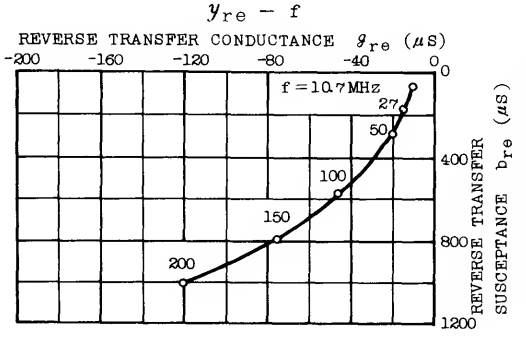


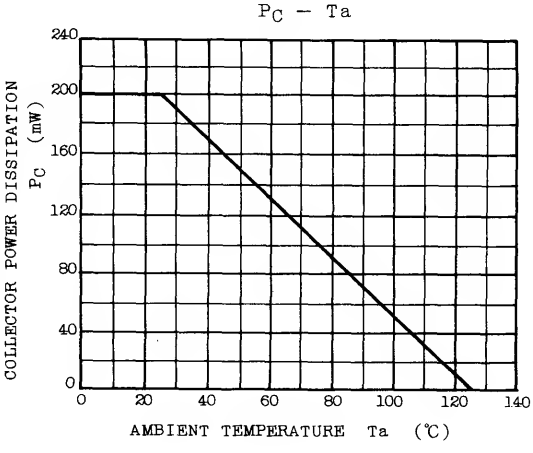

$|y_{rb}|, \theta_{rb} - V_{CB}$
PHASE ANGLE OF REVERSE TRANSFER ADMITTANCE θ_{rb} (°)
REVERSE TRANSFER ADMITTANCE $|y_{rb}|$ (mS)
$|y_{rb}|$
θ_{rb}
COMMON BASE
$I_E = -1mA$, f = 100MHz
Ta = 25℃
COLLECTOR-BASE VOLTAGE V_{CB} (V)


$y_{ie} - f$
INPUT SUSCEPTANCE b_{ie} (mS)
INPUT CONDUCTANCE g_{ie} (mS)
f = 200MHz
COMMON EMITTER
$V_{CE} = 6V$
$I_E = -1mA$
Ta = 25℃


$y_{oe} - f$
OUTPUT SUSCEPTANCE b_{oe} (mS)
OUTPUT CONDUCTANCE g_{oe} (μS)
COMMON EMITTER
$V_{CE} = 6V$
$I_E = -1mA$
Ta = 25℃
f = 200MHz


$y_{fe} - f$
FORWARD TRANSFER CONDUCTANCE g_{fe} (mS)
FORWARD TRANSFER SUSCEPTANCE b_{fe} (mS)
COMMON EMITTER
$V_{CE} = 6V$
$I_E = -1mA$
Ta = 25℃
f = 10.7MHz


$y_{re} - f$
REVERSE TRANSFER CONDUCTANCE g_{re} (μS)
REVERSE TRANSFER SUSCEPTANCE b_{re} (μS)
f = 10.7MHz


$P_C - Ta$
COLLECTOR POWER DISSIPATION P_C (mW)
AMBIENT TEMPERATURE Ta (℃)